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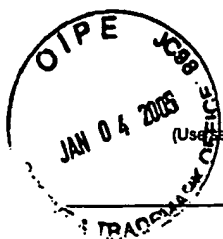
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

EP	"Low-temperature growth of piezoelectric AlN film by rf reactive planar magnetron sputtering", T. Shiosaki et al., Appl. Phys. Lett. 36(8), 15 April 1980, 643-645, © 1980 American Institute of Physics
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EP	"Deposition of AlN thin film using reactive sputtering method", Y. Honda et al., Reports of Kumamoto Industrial Research Institute No. 35, 1997, pp. 59-63 © Kumamoto Industrial Research Institute

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